METHOD OF FORMING COPPER INTERCONNECTS

ABSTRACT

A method of forming copper interconnects for an integrated circuit is provided. An antireflective coating layer is formed over an insulating layer formed over a semiconductor substrate. An interconnect pattern is patterned and etched into said insulating layer. A diffusion barrier layer is then conformally deposited in a deposition chamber along the etched interconnect pattern, wherein the antireflective coating is removed in said chamber before deposition of the barrier layer. Copper interconnects are then formed in the interconnect pattern etched in the insulating layer.

FIG. 5